

Growth of multiple non-compositional-graded layers

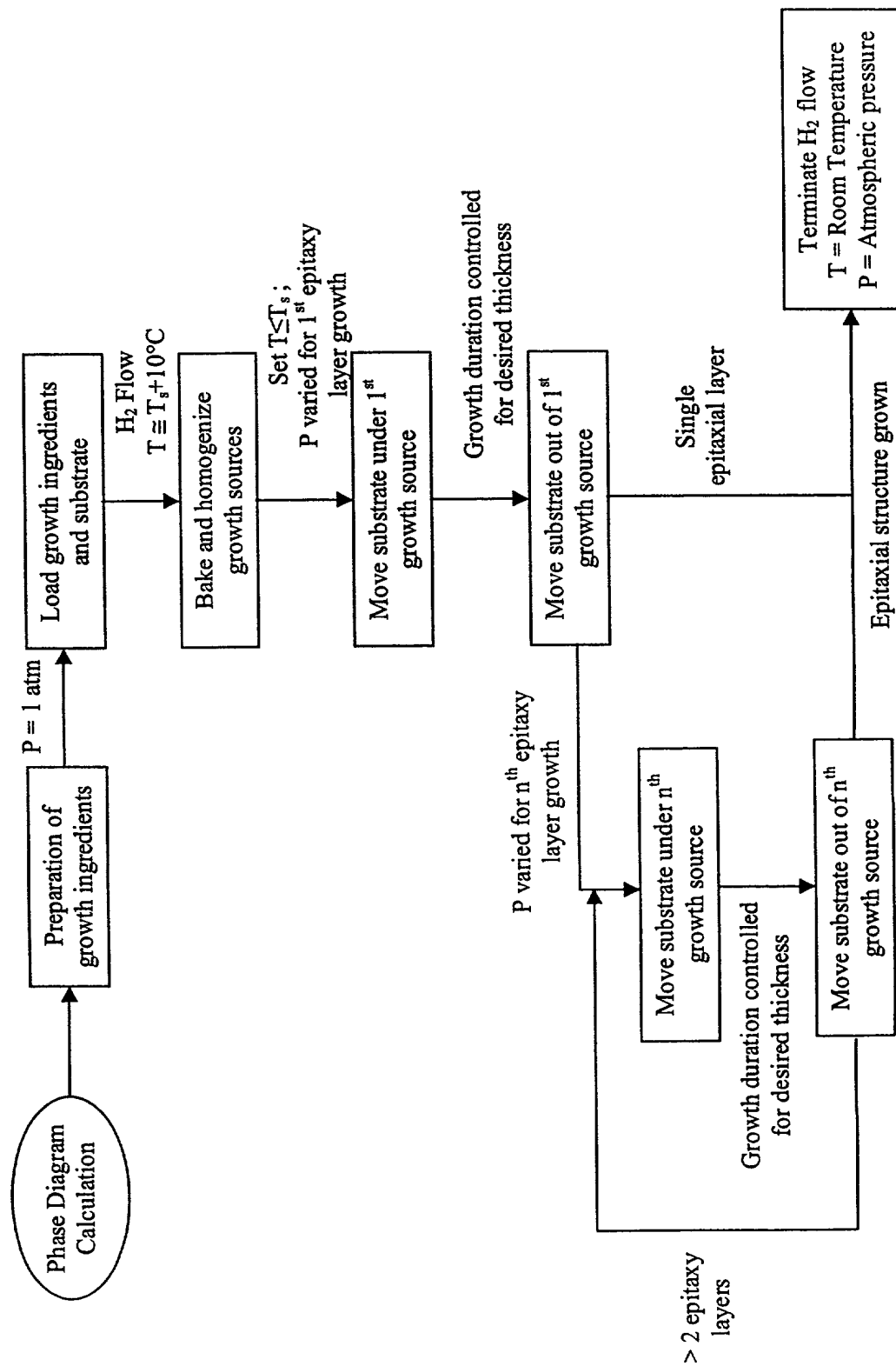


FIGURE 2

Growth of compositional-graded layer

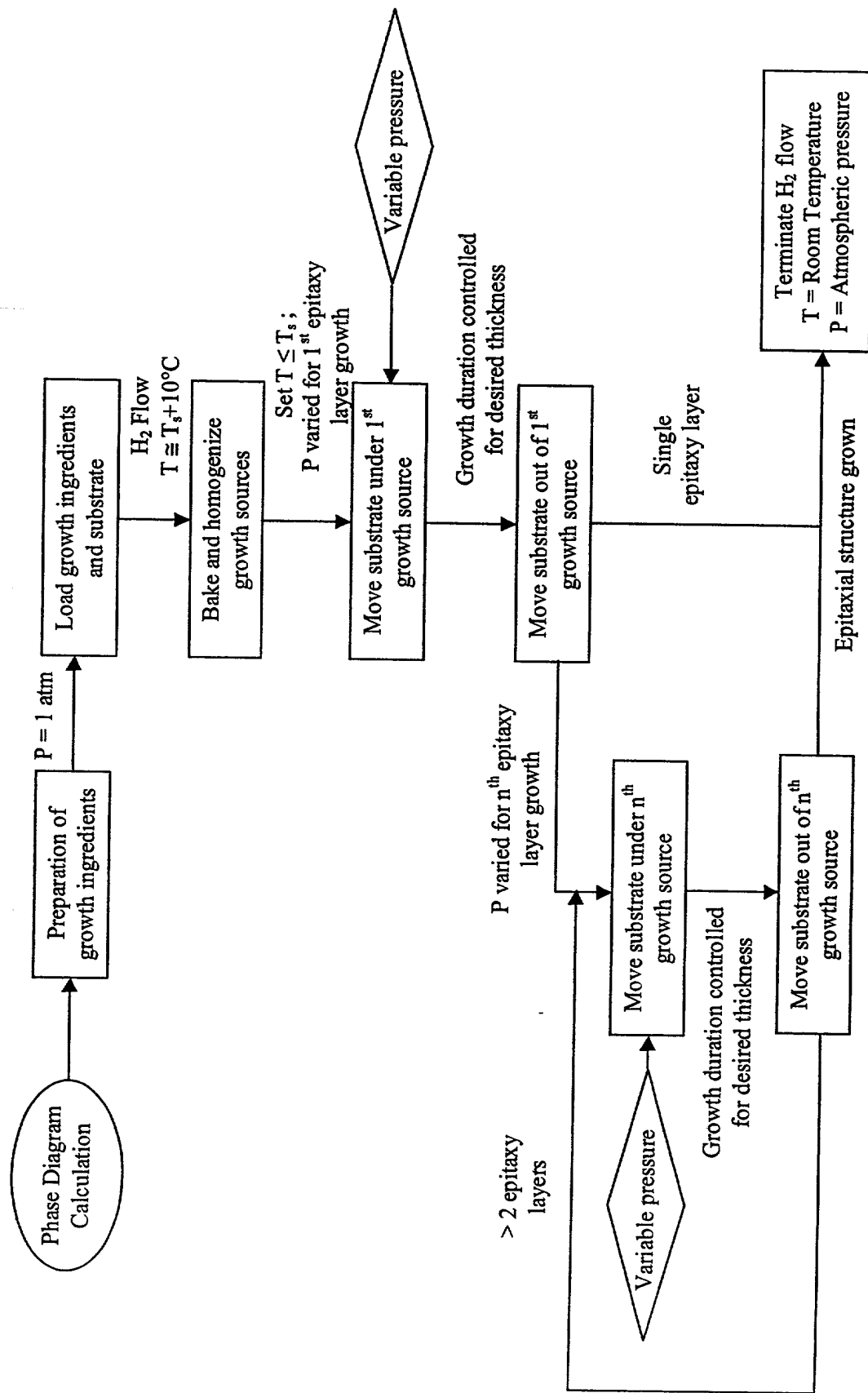


FIGURE 3 Schematic

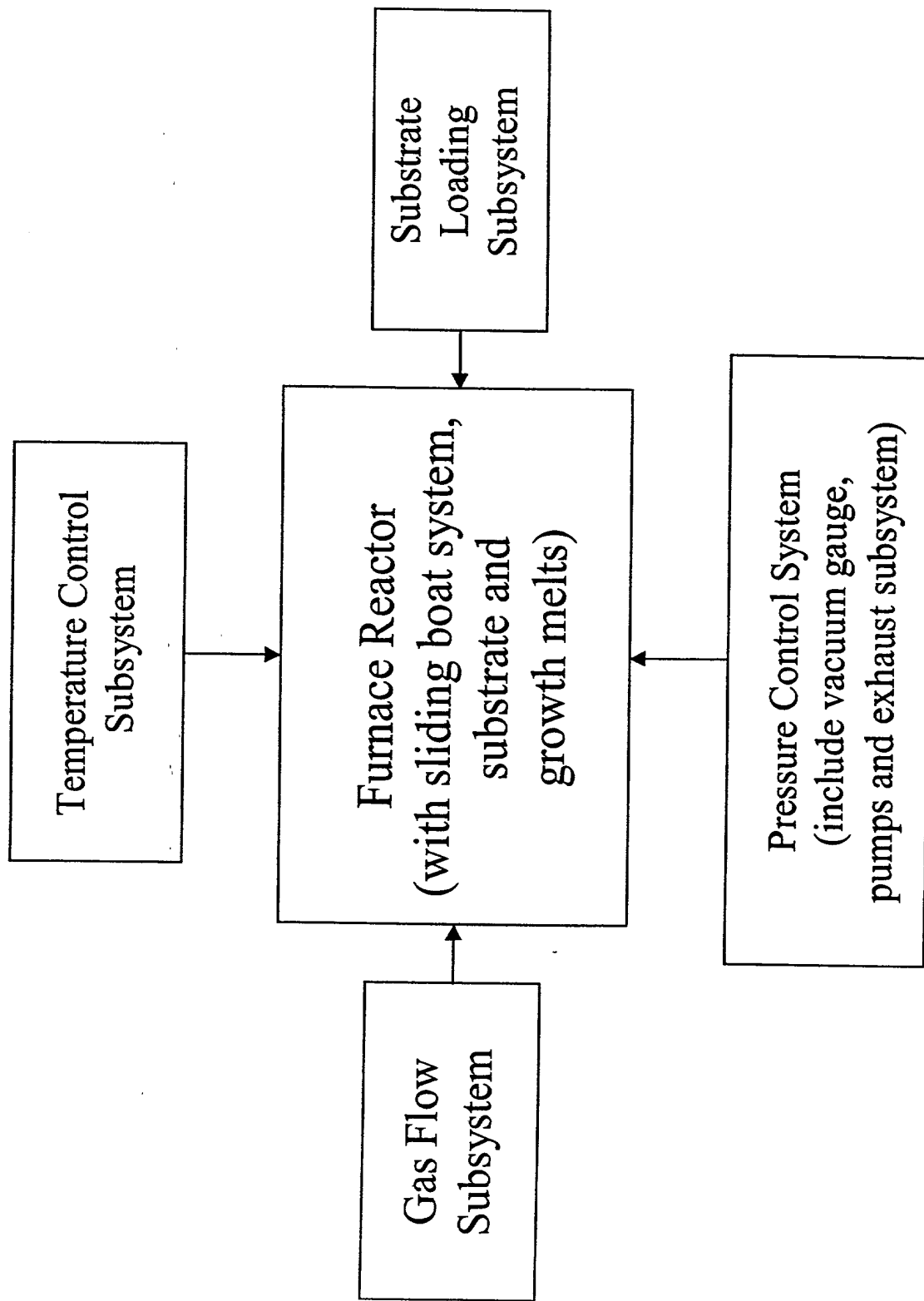
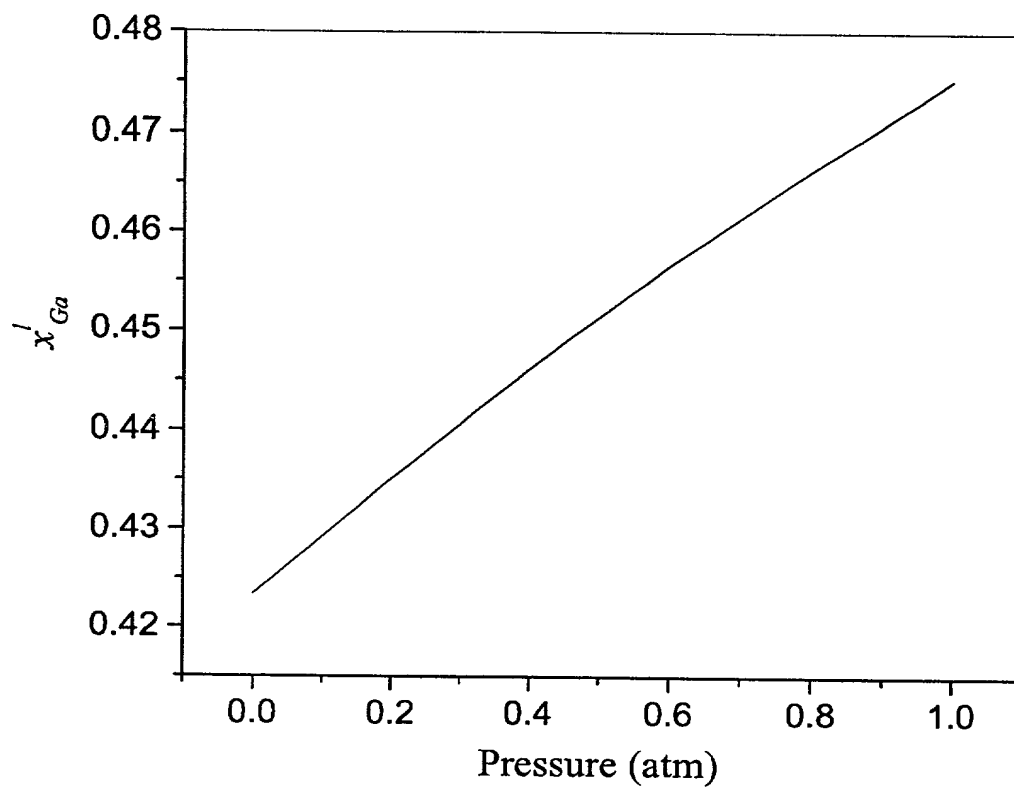
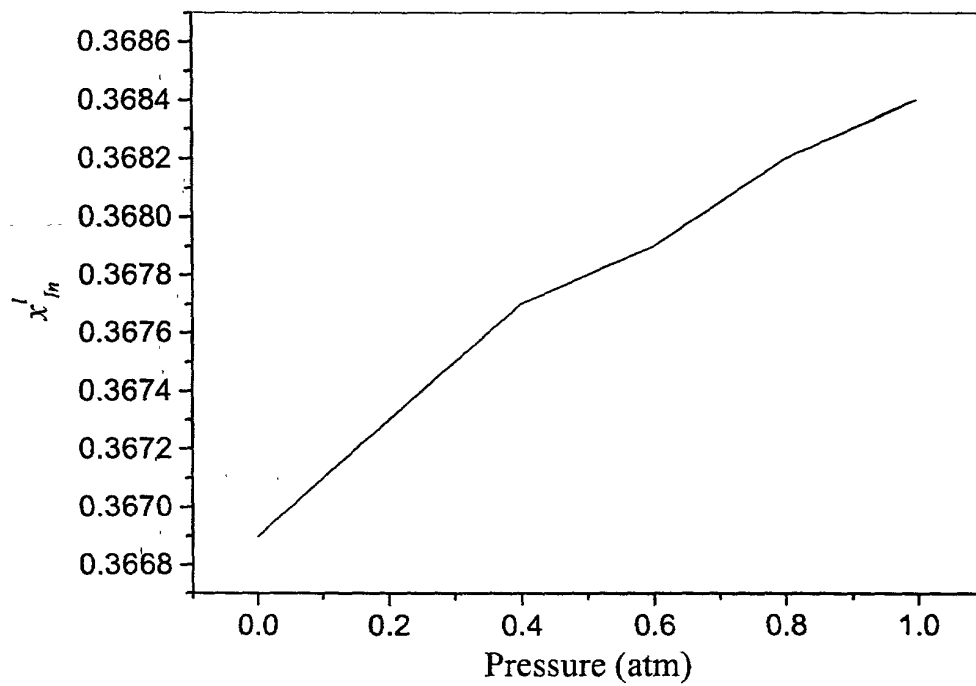


FIGURE 4



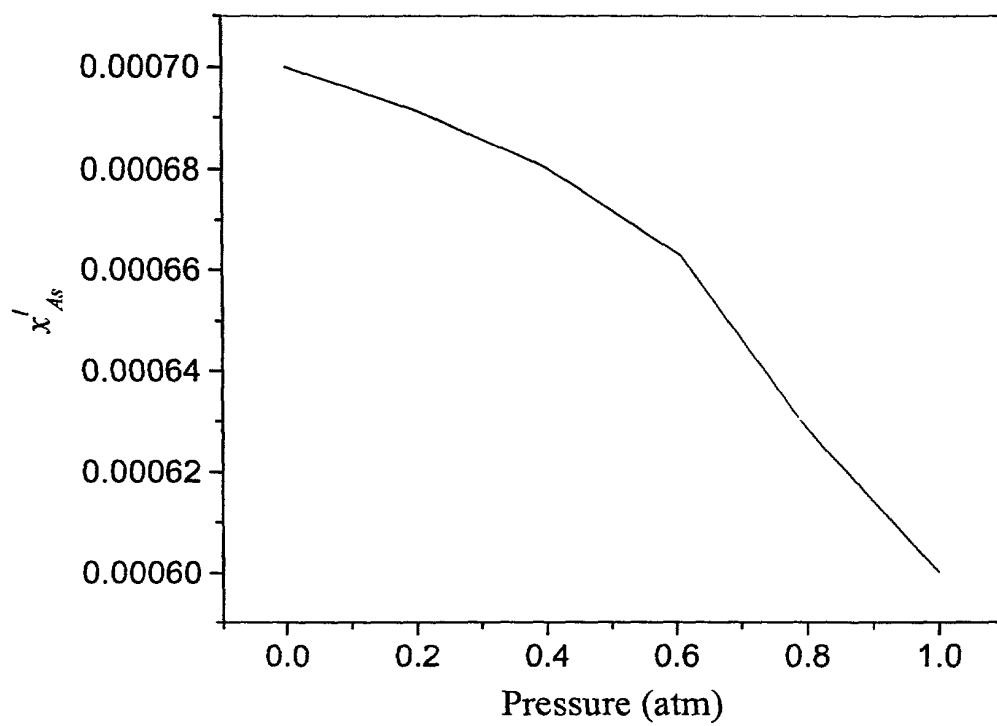
Atomic fraction x_{Ga}^I in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 5



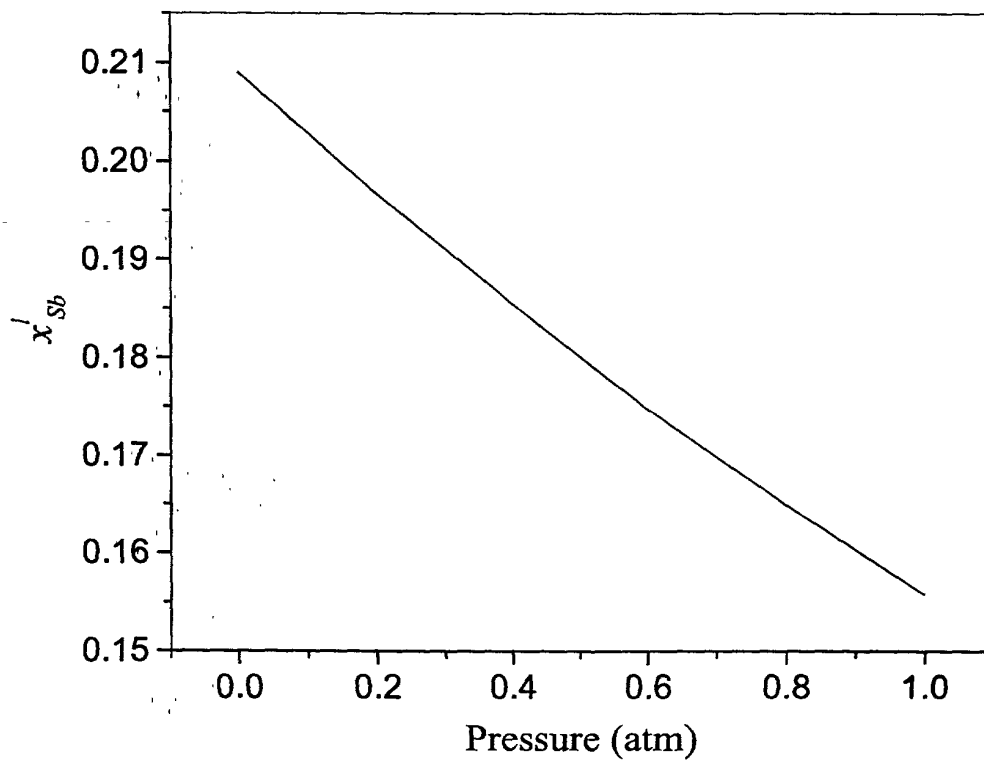
Atomic fraction x_{In}^I in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 6



Atomic fraction x'_{As} in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550 °C as a function of pressure.

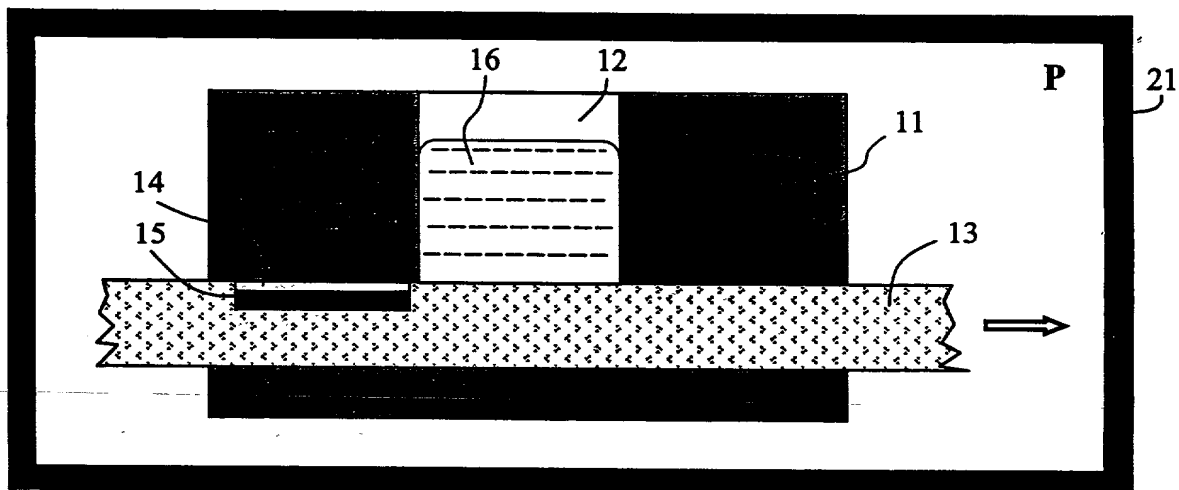
FIGURE 7



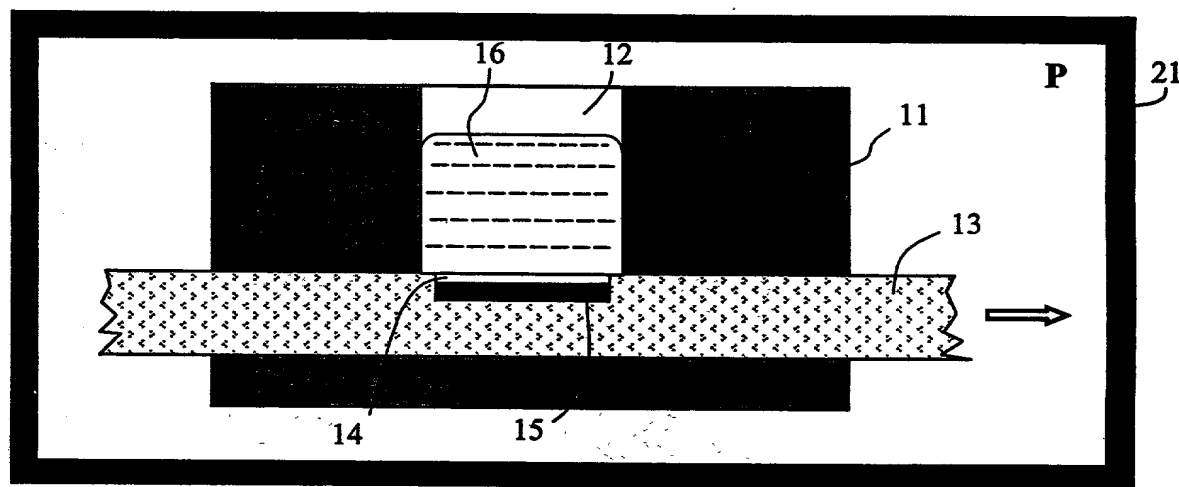
Atomic fraction x'_{Sb} in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 8

(a)



(b)



(c)

